NSN 5961-00-881-7060

Transistor - Page 1 of 1

No Fiig: A110a0



View Online at https://aerobasegroup.com/nsn/5961-00-881-7060 **Inclosure Material:** Metal **Overall Length:** 0.410 inches **Overall Diameter:** 0.800 inches **Mounting Facility Quantity: Internal Configuration:** Field effect **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Germanium **Voltage Rating In Volts Per Characteristic:** 50.0 breakdown voltage, collector-to-emitter, base open and 100.0 breakdown voltage, collector-to-base, emitter open and 50.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** 5.00 amperes base current, dc and 10.00 amperes collector current, dc **Power Rating Per Characteristic:** 90.0 watts collector power dissipation **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnp **Test Data Document:** 28527-2156874 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 1 case and 2 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:**